DIONICS INC.

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DTN9000, 9001
DTN9000T, 9001T

NPN HIGH VOLTAGE TRANSISTOR

MAXIMUM RATINGS

RATING		SYMBOL		UNIT
Collector – Emitter Voltage	9000 9001	V_{CEO}	400V 350V	V_{DC}
Collector – Base Voltage	9000 9001	V_{CB}	450V 400V	V_{DC}
Collector – Emitter Voltage	9000 9001	BV_{CER}	400V 350V	V_{DC}
Emitter – Base Voltage		BV_{EBO}	6	V_{DC}
Collector Current		I_C	500	mA
Operating & Storage Temperature		T_J, T_{STG}	-55° to + 150°C	

THERMAL CHARACTERISTICS

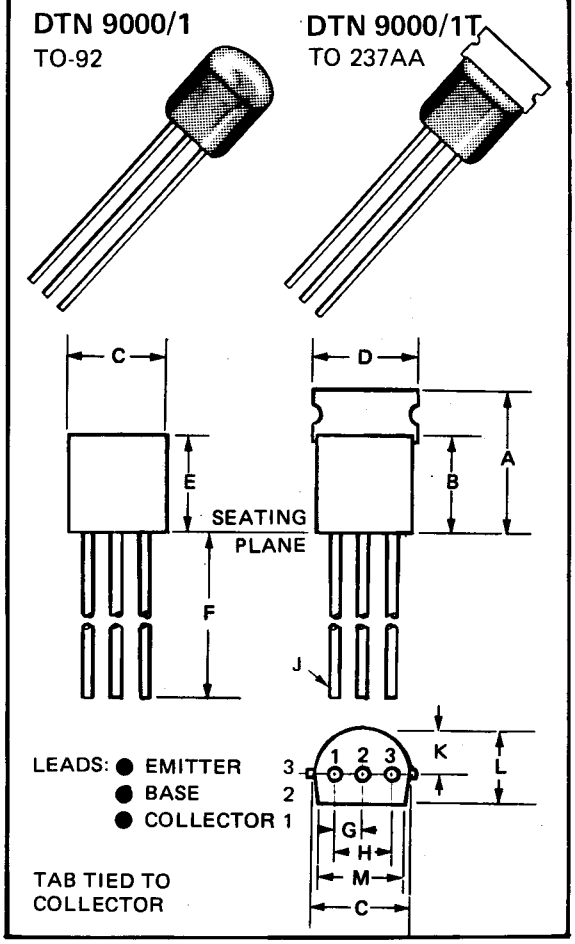
	DTN9000/1	DTN9000/1T	
Thermal Resistance			
Free Air	200	150	OC/W
Infinite Heat Sink	–	35	

ELECTRICAL CHARACTERISTICS T_C = 25°C

CHARACTERISTIC		SYMBOL	MIN	MAX	UNIT
Collector – Base Breakdown Voltage I_{CBO} = 100 μA	9000 9001	BV_{CBO}	450 400		V_{DC}
Collector – Emitter Breakdown Voltage I_C = 0.5mA, I_B = 0	9000 9001	BV_{CEO}	400 350		V_{DC}
Emitter – Base Breakdown Voltage I_{EBO} = 10μA		BV_{EBO}	6		V_{DC}
Collector – Base Cutoff Current V_{CBO} = 300V		I_{CBO}		200	nA
Collector – Base Cutoff Current V_{CE} = 300V, R_{BE} = 10KΩ		I_{CER}		2.0	μA
Current Gain Common Emitter V_{CE} = 10V, I_C = 5 mA	9000 9001	H_{FE}	20 30		
Current Gain Common Emitter V_{CE} = 10V, I_C = 20 mA	9000 9001	H_{FE}	30 40		
Collector – Emitter Saturation Voltage I_C = 20mA I_B = 2mA		$V_{CE(SAT)}$		0.5	V_{DC}
Base – Emitter – Saturation Voltage I_C = 20mA, I_B = 2mA		$V_{BE(SAT)}$		1.3	V_{DC}
Current – Gain Bandwidth Product I_C = 10mA, V_{CE} = 10V f = 5.0 mHz		f_t	35 TYP		MHz

DTN 9000/1
TO-92

DTN 9000/1T
TO 237AA



SYMBOL	INCHES	MILLIMETERS
A	.260/.270	6.60/6.86
B	.175/.185	4.44/4.70
C	.175/.205	4.96/5.20
D	.195/.205	4.95/5.21
E	.170/.210	4.58/5.33
F	.50 MIN	12.70 MIN
G	.045/.055	1.14/1.40
H	.095/.105	2.41/2.67
J	.016/.021	.41/.533
K	.08/.105	2.03/2.67
L	.125/.165	3.94/4.19
M	.135 MIN	3.43 MIN.

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